



## TO-220 Plastic-Encapsulated Transistors

### 2SA940 TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$$P_{CM} : 1.5 \text{ W (Tamb=25°C)}$$

Collector current

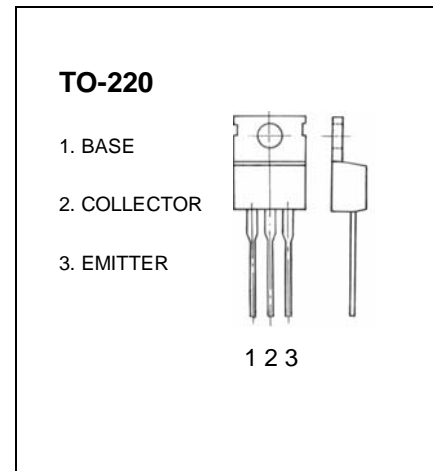
$$I_{CM} : -1.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -150 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55°C \text{ to } +150°C$$



#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-150			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -120V, I_E = 0$			-10	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$			-10	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE} = -10V, I_C = -500mA$	40		140	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			-1.5	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -10V, I_C = -500mA$	-0.65		-0.85	V
Transition frequency	$f_T$	$V_{CE} = -10V, I_C = -500mA$		4		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$		55		pF